PN2222A is a Preferred Device

General Purpose Transistors

NPN Silicon

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector-Emitter Voltage	PN2222 PN2222A	V _{CEO}	30 40	Vdc
Collector-Base Voltage	PN2222 PN2222A	V _{CBO}	60 75	Vdc
Emitter-Base Voltage	PN2222 PN2222A	V _{EBO}	5.0 6.0	Vdc
Collector Current – Contin	uous	I _C	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C		P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C		P _D	1.5 12	Watts mW/°C
Operating and Storage Juli Temperature Range	nction	T _J , T _{stg}	-55 to +150	°C

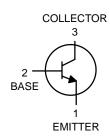
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	83.3	°C/W



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MARKING DIAGRAM



TO-92 CASE 29 STYLE 1

PN222x= Device Code x = 2 or A

= Year

WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
PN2222	TO-92	5000 Units/Box
PN2222A	TO-92	5000 Units/Box
PN2222ARLRA	TO-92	2000/Tape & Reel
PN2222ARLRM	TO-92	2000/Ammo Pack
PN2222ARLRP	TO-92	2000/Ammo Pack

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS		- 1			
Collector–Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	PN2222 PN2222A	V _{(BR)CEO}	30 40	_ _	Vdc
Collector–Base Breakdown Voltage ($I_C = 10 \mu Adc, I_E = 0$)	PN2222 PN2222A	V _{(BR)CBO}	60 75	_ _	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	PN2222 PN2222A	V _{(BR)EBO}	5.0 6.0		Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	PN2222A	I _{CEX}	-	10	nAdc
Collector Cutoff Current $(V_{CB} = 50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 50 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$ $(V_{CB} = 50 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$	PN2222 PN2222A PN2222 PN2222A	Ісво	- - - -	0.01 0.01 10 10	μAdc
Emitter Cutoff Current (V _{EB} = 3.0 Vdc, I _C = 0)	PN2222A	I _{EBO}	_	100	nAdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	PN2222A	I _{BL}	-	20	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{array}{l} (I_C=0.1 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}, T_A=-55^{\circ}C) \\ (I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \text{ (Note 1.)} \\ (I_C=150 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \text{ (Note 1.)} \\ (I_C=500 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \text{ (Note 1.)} \\ \end{array} $	PN2222A only PN2222 PN2222A	h _{FE}	35 50 75 35 100 50 30 40	- - - 300 - -	1
Collector–Emitter Saturation Voltage (Note 1.) (I _C = 150 mAdc, I _B = 15 mAdc)	PN2222 PN2222A	V _{CE(sat)}	- -	0.4 0.3	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	PN2222 PN2222A		_	1.6 1.0	
Base–Emitter Saturation Voltage (Note 1.) (I _C = 150 mAdc, I _B = 15 mAdc)	PN2222 PN2222A	V _{BE(sat)}	_ 0.6	1.3 1.2	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	PN2222 PN2222A		- -	2.6 2.0	

^{1.} Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic			Symbol	Min	Max	Unit
SMALL-SIGNAL	. CHARACTERISTICS					•
Current–Gain – Bandwidth Product (Note 2.) (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 MHz) PN2222 PN2222A		f _T	250 300	 _	MHz	
Output Capacitance (V _{CB} = 10 Vdc, I _F = 0, f = 1.0 MHz)			C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz) PN2222 PN2222A			C _{ibo}	- -	30 25	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz) PN2222A (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz) PN2222A		h _{ie}	2.0 0.25	8.0 1.25	kΩ	
$\label{eq:Voltage Feedback Ratio} $		h _{re}	- -	8.0 4.0	X 10 ⁻⁴	
	ent Gain V _{CE} = 10 Vdc, f = 1.0 kHz) / _{CE} = 10 Vdc, f = 1.0 kHz)	PN2222A PN2222A	h _{fe}	50 75	300 375	-
Output Admittance $(I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$ PN2222A $(I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$ PN2222A		h _{oe}	5.0 25	35 200	μmhos	
Collector Base Tin (I _E = 20 mAdc, \	ne Constant / _{CB} = 20 Vdc, f = 31.8 MHz)	PN2222A	rb′C _c	-	150	ps
Noise Figure $(I_C = 100 \ \mu Adc, \ V_{CE} = 10 \ Vdc, \ R_S = 1.0 \ k\Omega, \ f = 1.0 \ kHz) \qquad PN2222A$		NF	-	4.0	dB	
SWITCHING CH	ARACTERISTICS PN2222A or	nly			•	•
Delay Time	Delay Time $(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -0.5 \text{ Vdc},$		t _d	-	10	ns
Rise Time	$I_C = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc})$ (t _r		25	ns
Storage Time	ge Time $(V_{CC} = 30 \text{ Vdc}, I_C = 150 \text{ mAdc},$		t _s	_	225	ns
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$ (Figure 2)		t _f	_	60	ns

^{2.} f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

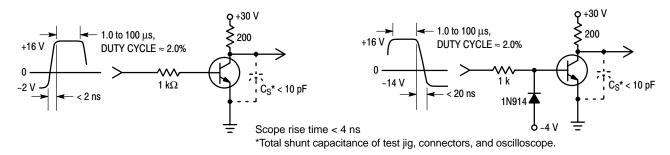


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

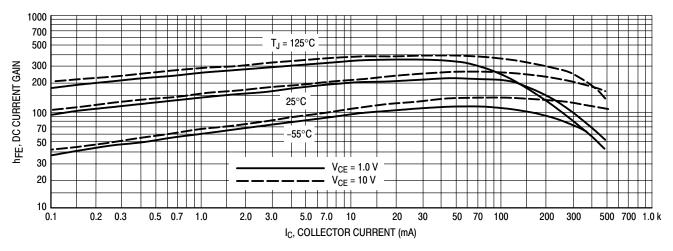


Figure 3. DC Current Gain

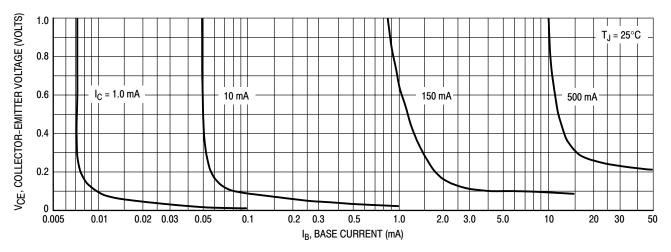


Figure 4. Collector Saturation Region

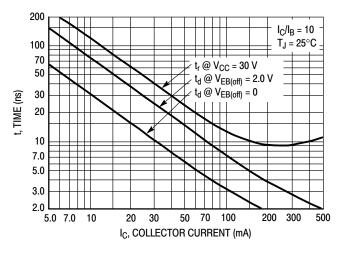


Figure 5. Turn-On Time

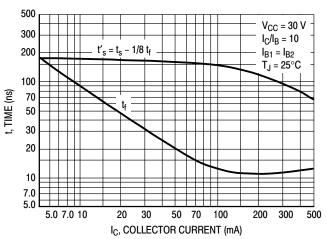
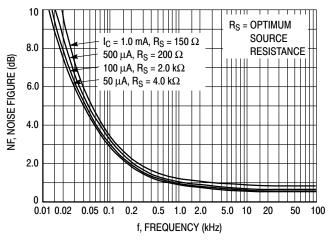


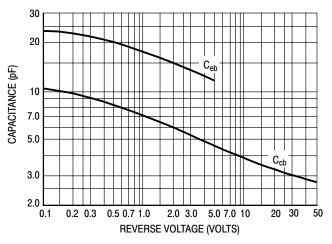
Figure 6. Turn-Off Time



8.0 $I_C = 50 \mu A$ NF, NOISE FIGURE (dB) $100 \, \mu A$ 500 μΑ 6.0 1.0 mA 4.0 2.0 50 100 200 1.0 k 2.0 k 5.0 k 10 k 20 k 50 k 100 k R_S, SOURCE RESISTANCE (OHMS)

Figure 7. Frequency Effects

Figure 8. Source Resistance Effects



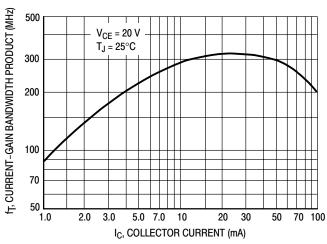
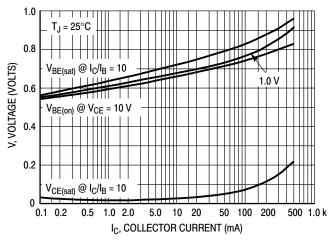


Figure 9. Capacitances

Figure 10. Current-Gain Bandwidth Product



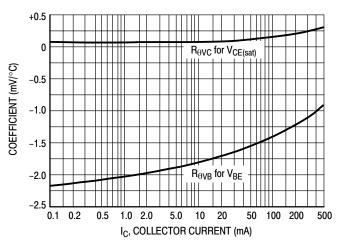
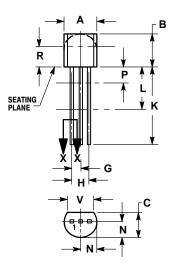


Figure 11. "On" Voltages

Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 TO-226AA CASE 29-11 **ISSUE AL**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR



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